



MiniSKiiP® 0

1-phase bridge rectifier +
brake chopper + 3-phase
bridge inverter
SKiiP 03NEB066V3

Features

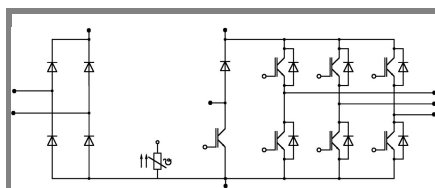
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 5,6 kVA
- Typical motor power 3,0 kW

Remarks

- Case temperature limited to $T_C = 125^\circ\text{C}$ max.
- Product reliability results are valid for $T_j = 150^\circ\text{C}$
- SC data: $t_p \leq 6 \mu\text{s}$; $V_{GE} \leq 15 \text{ V}$; $T_j = 150^\circ\text{C}$; $V_{CC} = 360 \text{ V}$
- V_{CEsat} , V_F = chip level value



NEB

Absolute Maximum Ratings		T _s = 25 °C, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V _{CES}		600	V
I _C	T _s = 25 (70) °C, T _j = 150 °C	25 (17)	A
I _C	T _s = 25 (70) °C, T _j = 175 °C	27 (21)	A
I _{CRM}	t _p = 1 ms	30	A
V _{GES}		± 20	V
Diode - Inverter, Chopper			
I _F	T _s = 25 (70) °C, T _j = 150 °C	24 (16)	A
I _F	T _s = 25 (70) °C, T _j = 175 °C	28 (21)	A
I _{FRM}	t _p = 1 ms	30	A
Diode - Rectifier			
V _{RRM}		800	V
I _F	T _s = 70 °C	35	A
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	220	A
i ² t	t _p = 10 ms, sin 180 °, T _j = 25 °C	240	A ² s
I _{tRMS}	per power terminal (20 A / spring)	20	A
T _j	IGBT, Diode	-40...+175	°C
T _{stg}		-40...+125	°C
V _{isol}	AC, 1 min.	2500	V

Characteristics				$T_s = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
$V_{CE(sat)}$	$I_{Cnom} = 15 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$		1,45 (1,65)	1,85 (2,05)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1 \text{ mA}$		5,8		V
$V_{CE(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,85)	1 (0,9)	V
r_{CE}	$T_j = 25 (150)^\circ\text{C}$		40 (57)	60 (80)	$\text{m}\Omega$
C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		0,86		nF
C_{oes}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		0,18		nF
C_{res}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		0,12		nF
$R_{CC'+EE'}$	spring contact-chip $T_s = 25 (150)^\circ\text{C}$				$\text{m}\Omega$
$R_{th(j-s)}$	per IGBT		1,8		K/W
$t_{d(on)}$	under following conditions		20		ns
t_r	$V_{CC} = 300 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$		30		ns
$t_{d(off)}$	$I_{Cnom} = 15 \text{ A}$, $T_j = 150^\circ\text{C}$		155		ns
t_f	$R_{Gon} = R_{Goff} = 22 \Omega$		45		ns
$E_{on} (E_{off})$	inductive load		0,6 (0,5)		mJ
Diode - Inverter, Chopper					
$V_F = V_{EC}$	$I_F = 15 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$		1,4 (1,4)	1,7 (1,7)	V
$V_{(TO)}$	$T_j = 25 (150)^\circ\text{C}$		1 (0,9)	1,1 (1)	V
r_T	$T_j = 25 (150)^\circ\text{C}$		27 (34)	40 (47)	$\text{m}\Omega$
$R_{th(j-s)}$	per diode		2,5		K/W
I_{RRM}	under following conditions		19,8		A
Q_{rr}	$I_{Fnom} = 15 \text{ A}$, $V_R = 300 \text{ V}$		1,9		μC
E_{rr}	$V_{GE} = 0 \text{ V}$, $T_j = 150^\circ\text{C}$		0,5		mJ
	$di_F/dt = 930 \text{ A}/\mu\text{s}$				
Diode - Rectifier					
V_F	$I_{Fnom} = 15 \text{ A}$, $T_j = 25^\circ\text{C}$		1,1		V
$V_{(TO)}$	$T_j = 150^\circ\text{C}$		0,8		V
r_T	$T_j = 150^\circ\text{C}$		20		$\text{m}\Omega$
$R_{th(j-s)}$	per diode		1,5		K/W
Temperature Sensor					
R_{ts}	3 %, $T_r = 25 (100)^\circ\text{C}$		1000(1670)		Ω
Mechanical Data					
w			21,5		g
M_s	Mounting torque	2		2,5	Nm

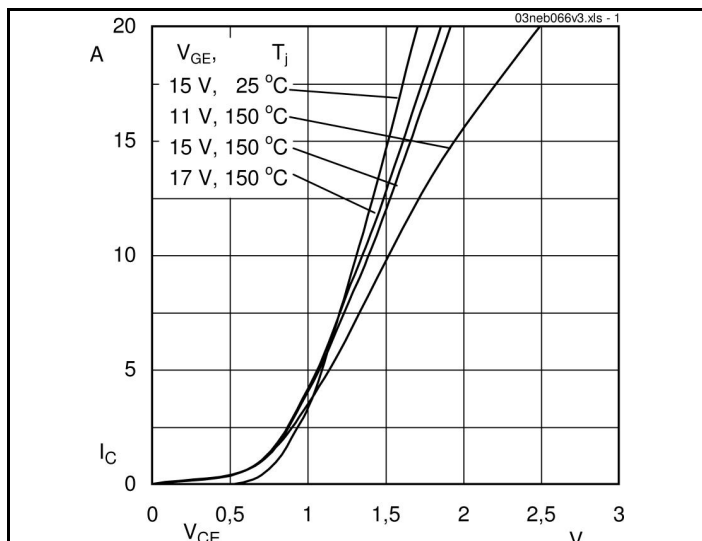


Fig. 1 Typ. output characteristic

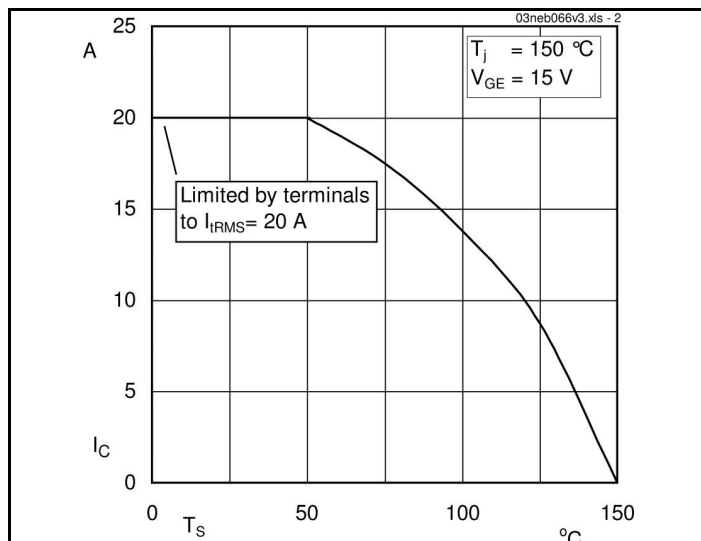


Fig. 2 Typ. rated output current

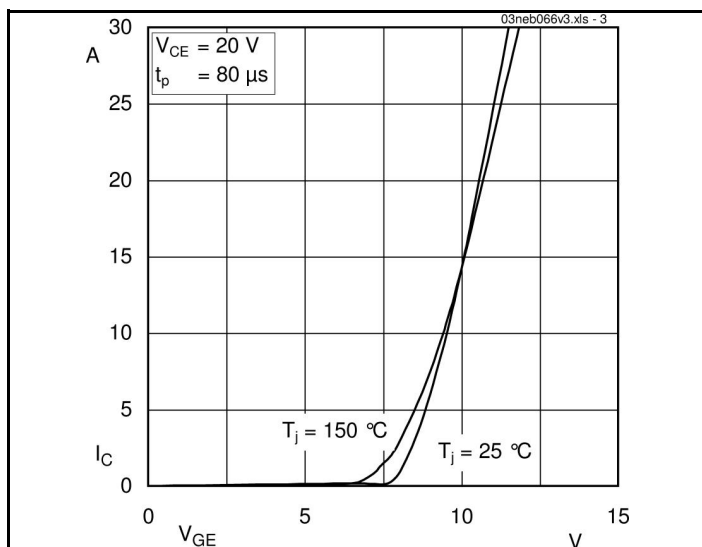


Fig. 3 Typ. transfer characteristic

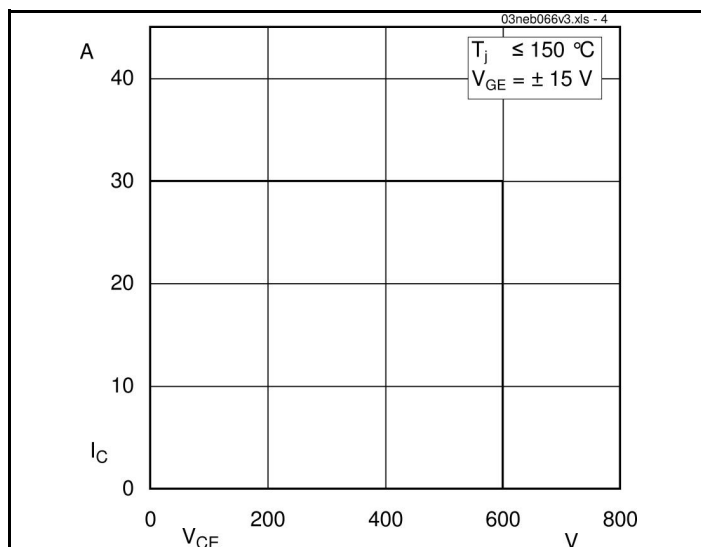


Fig. 4 Reverse bias safe operating area

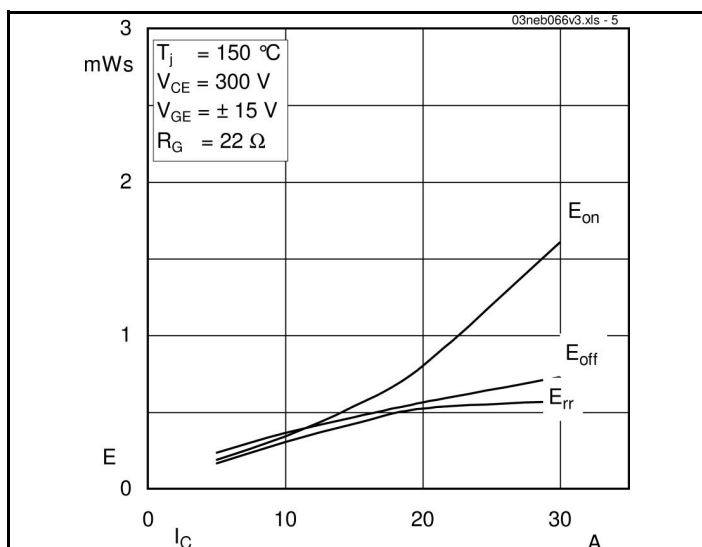


Fig. 5 Typ. Turn-on /-off energy = $f(I_C)$

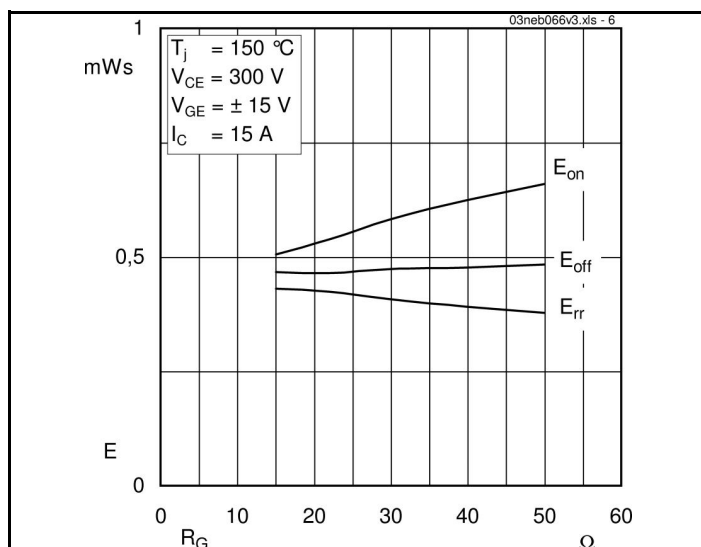


Fig. 6 Typ. Turn-on /-off energy = $f(R_G)$

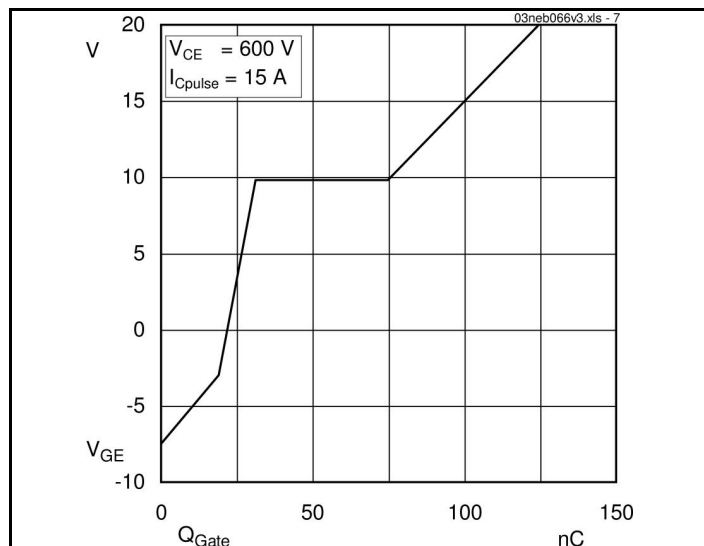


Fig. 7 Typ. gate charge characteristic

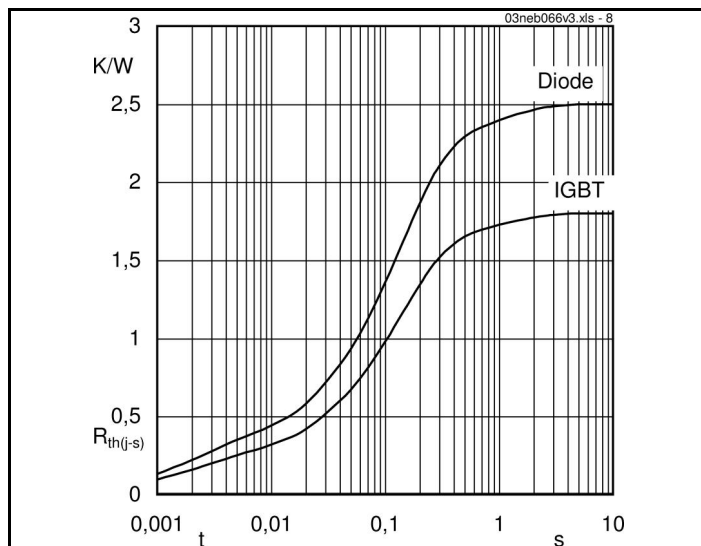


Fig. 8 Typ. thermal impedance

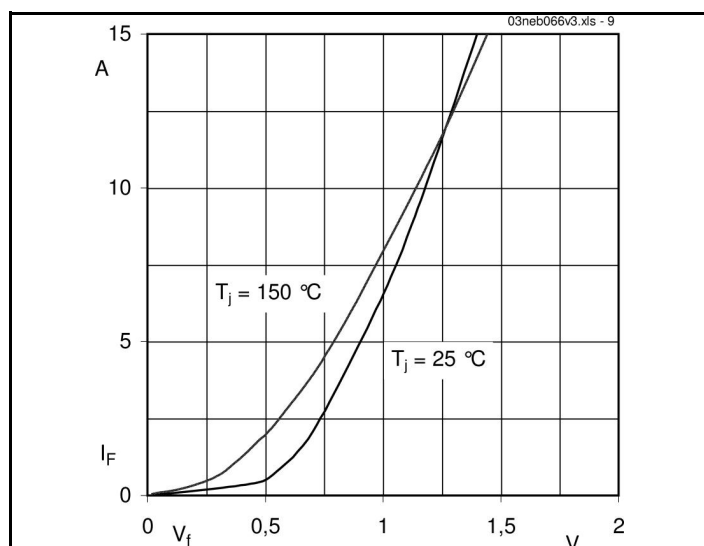


Fig. 9 Typ. freewheeling diode forward characteristic

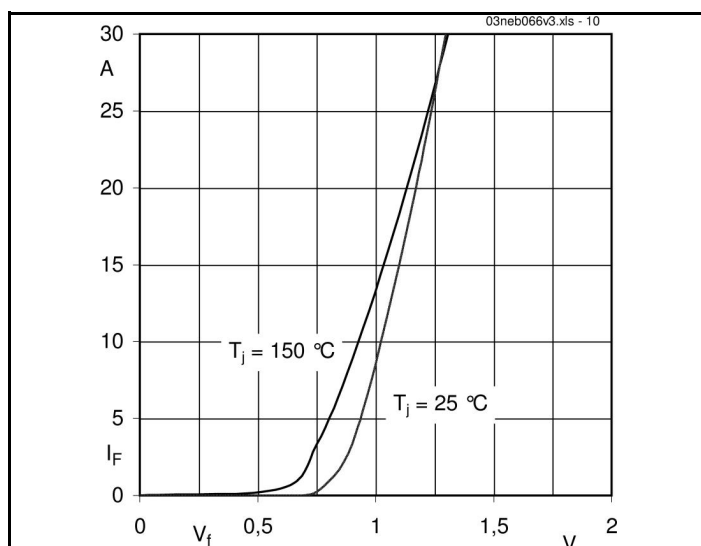
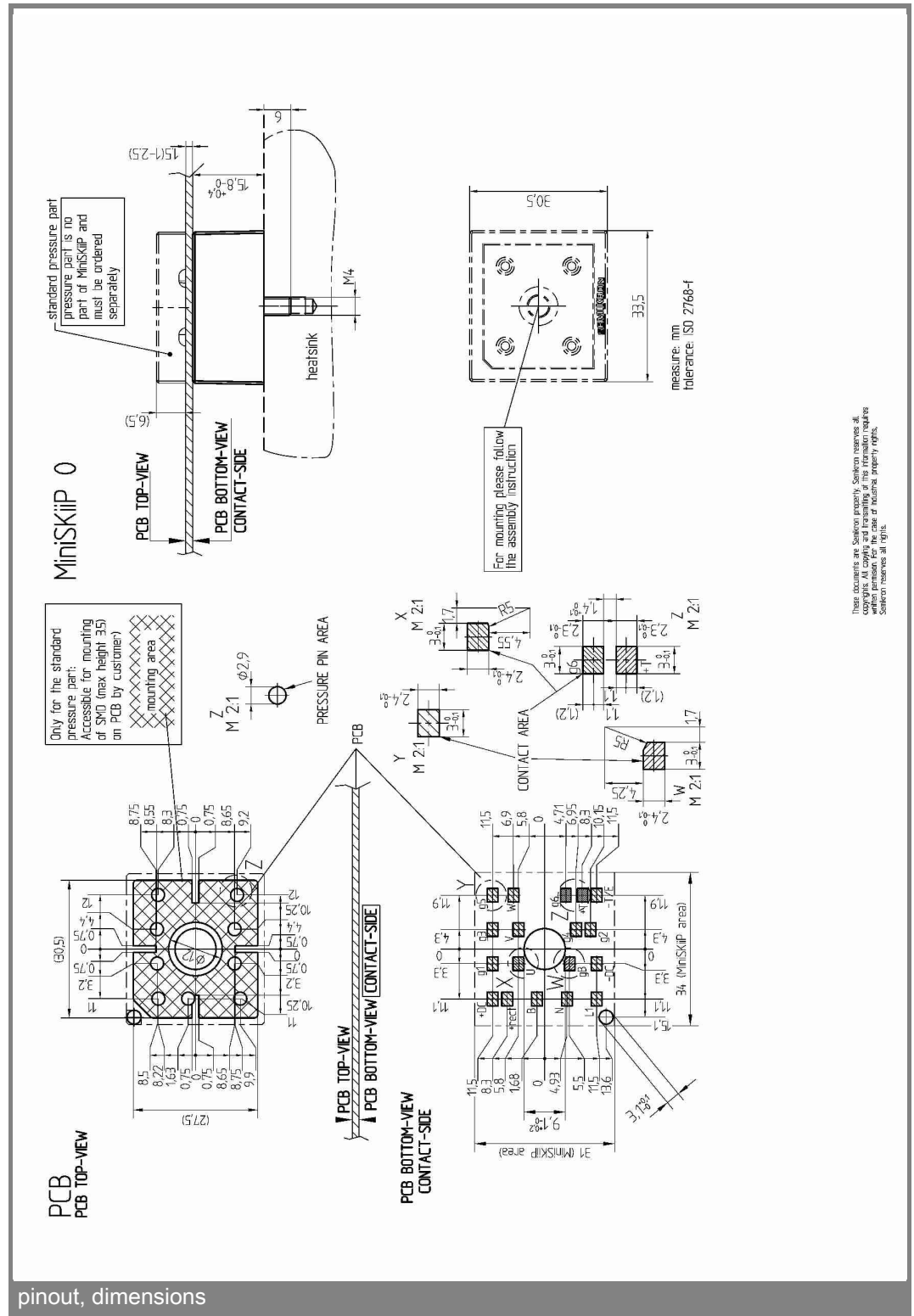
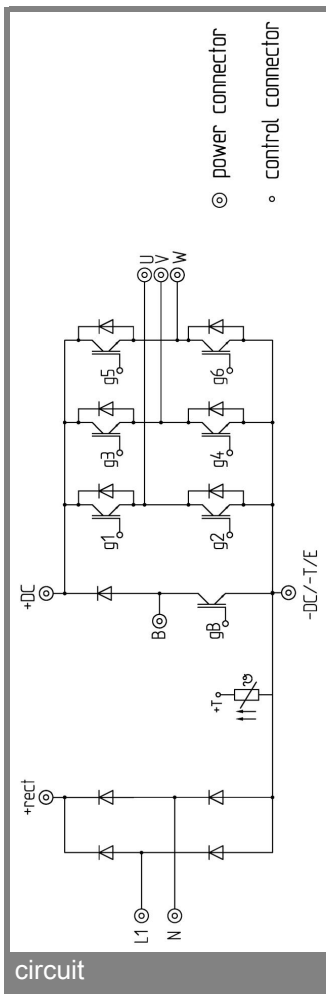


Fig. 10 Typ. input bridge forward characteristic



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.